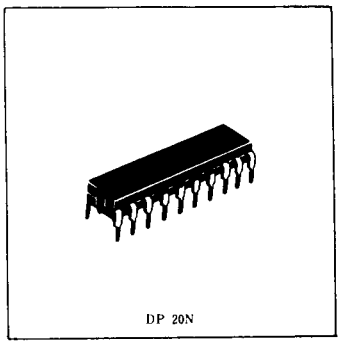
HM6167 Series

Maintenance Only
(Substitute HM6267P)

16384-word x 1-bit High Speed CMOS Static RAM

■FEATURES

- Single +5V Supply and High Density 20 Pin Package
- Fast Access Time – 85ns/100ns
- Low Power Stand-by and Low Power Operation
  Stand-by 100μW typ./5μW typ. (L-version)
  and Operating 150mW typ.
- Completely Static Memory . . . . . No Clock nor Refresh Required
- Fully TTL Compatible – All Inputs and Output
- Separate Data Input and Output . . . . . Three State Output
- Pin-Out Compatible with Intel 2167 Series
- Capability of Battery Back Up Operation (L-version)

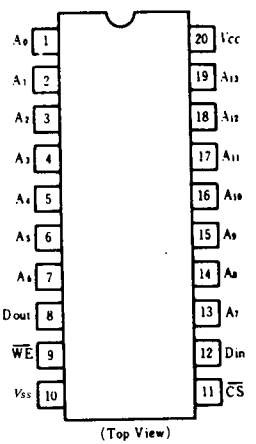


DP 20N

■ORDERING INFORMATION

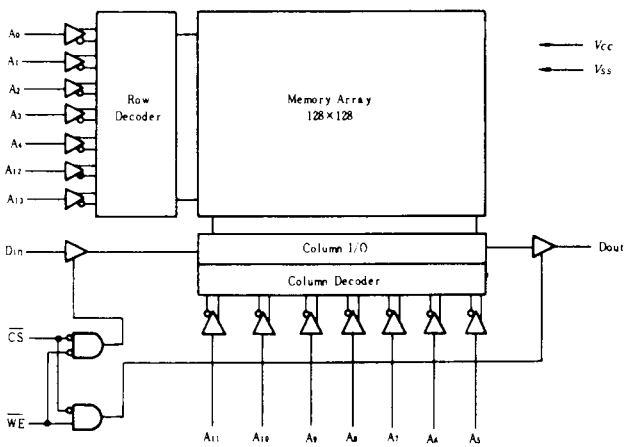
Type No.	Access Time	Package
HM6167P-6 HM6167P-8	85ns 100ns	300mil 20pin Plastic DIP
HM6167LP-6 HM6167LP-8	85ns 100ns	

■PIN ARRANGEMENT



(Top View)

■BLOCK DIAGRAM



■ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Terminal Voltage with Respect to V_{SS}	V_T	−0.5*1 to +7.0	V
Power Dissipation	P_T	1.0	W
Operating Temperature	T_{opr}	0 to +70	°C
Storage Temperature	T_{stg}	−55 to +125	°C
Storage Temperature under bias	$T_{stg(bias)}$	−10 to +85	°C

Note) *1. −3.5V for pulse width≦20ns

■RECOMMENDED DC OPERATING CONDITIONS

(0°C ≦ Ta ≦ 70°C)

Item	Symbol	min	typ	max	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input High Voltage	V_{IH}	2.2	—	6.0	V
Input Low Voltage	V_{IL}	−0.3*1	—	0.8	V

Note) *1. −3.0V for pulse width ≦ 20ns.

■TRUTH TABLE

$\overline{CS}$	$\overline{WE}$	Mode	V_{CC} Current	Output Pin	Reference Cycle
H	×	Not Selected	I_{SB}, I_{SB1}	High Z	
L	H	Read	I_{CC}	Dout	Read Cycle 1, 2
L	L	Write	I_{CC}	High Z	Write Cycle 1, 2

■DC AND OPERATING CHARACTERISTICS (V_{CC} = 5V ± 10%, Ta = 0°C to +70°C)

Item	Symbol	Test Conditions	min	typ*1	max	Unit
Input Leakage Current	$\|I_{LI}\|$	V_{CC} = 5.5V, V_{IN} = 0V ~ V_{CC}	—	—	2	μA
Output Leakage Current	$\|I_{LO}\|$	$\overline{CS}$ = V_{IH}, V_{OUT} = 0V ~ V_{CC}	—	—	2	μA
Operating Power Supply Current	I_{CC}	$\overline{CS}$ = V_{IL}, Output Open	—	30	60	mA
Standby Power Supply Current	I_{SB}	$\overline{CS}$ = V_{IH}	—	5	20	mA
	I_{SB1}	$\overline{CS}$ = V_{CC} − 0.2V	—	0.02	2	mA
		V_{IN} ≦ 0.2V or V_{IN} ≧ V_{CC} − 0.2V	—	1*2	50*2	μA
Output Low Voltage	V_{OL}	I_{OL} = 8mA	—	—	0.4	V
Output High Voltage	V_{OH}	I_{OH} = −4mA	2.4	—	—	V

Notes) *1. Typical limits are at V_{CC} = 5.0V, Ta = 25°C and specified loading.
*2. This characteristics is guaranteed only for L-version.

■CAPACITANCE (Ta = 25°C, f = 1.0MHz)

Item	Symbol	max	Unit	Conditions
Input Capacitance	C_{IN}	5	pF	V_{IN} = 0V
Output Capacitance	C_{OUT}	6	pF	V_{OUT} = 0V

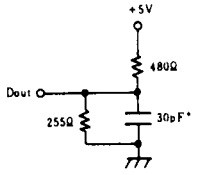
Note) This parameter is sampled and not 100% tested.

■AC CHARACTERISTICS (V_{CC} = 5V ± 10%, Ta = 0 to +70°C, unless otherwise noted)

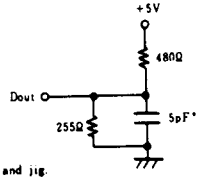
●AC TEST CONDITIONS

Input pulse levels: V_{SS} to 3.0V
Input rise and fall times: 5 ns
Input timing reference levels: 1.5V
Output reference levels: 1.5V
Output load: See Figure

Output Load A



Output Load B
(for t_{HZ}, t_{LZ}, t_{WZ} & t_{OW})



* Including scope and jig.

●READ CYCLE

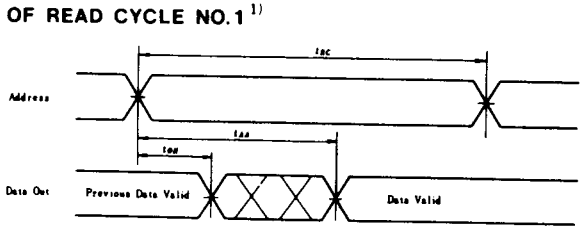
Item	Symbol	HM6167-6		HM6167-8		Unit
		min	max	min	max	
Read Cycle Time	t_{RC}	85	–	100	–	ns
Address Access Time	t_{AA}	–	85	–	100	ns
Chip Select Access Time	t_{ACS}	–	85	–	100	ns
Output Hold from Address Change	t_{OH}	5	–	5	–	ns
Chip Selection to Output in Low Z	t_{LZ}	5	–	5	–	ns
Chip Deselection to Output in High Z	t_{HZ}	0	40	0	40	ns
Chip Selection to Power Up Time	t_{PU}	0	–	0	–	ns
Chip Deselection to Power Down Time	t_{PD}	–	40	–	45	ns

●WRITE CYCLE

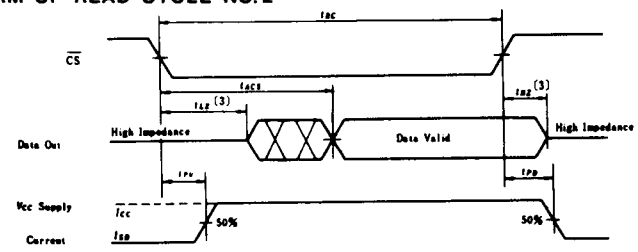
Item	Symbol	HM6167-6		HM6167-8		Unit	Notes
		min	max	min	max		
Write Cycle Time	t_{WC}	85	–	100	–	ns	2
Chip Selection to End of Write	t_{CW}	65	–	80	–	ns	
Address Valid to End of Write	t_{AW}	65	–	80	–	ns	
Address Setup Time	t_{AS}	0	–	0	–	ns	
Write Pulse Width	t_{WP}	45	–	55	–	ns	
Write Recovery Time	t_{WR}	0	–	0	–	ns	
Data Valid to End of Write	t_{DW}	35	–	40	–	ns	
Data Hold Time	t_{DH}	0	–	0	–	ns	
Write Enable to Output in High Z	t_{WZ}	0	40	0	40	ns	3, 4
Output Active from End of Write	t_{OW}	0	–	0	–	ns	3, 4

Notes) 1. If $\overline{CS}$ goes high simultaneouly with $\overline{WE}$ high, the output remains in a high impedance state.
2. All Write Cycle timings are referenced from the last valid address to the first transitioning address.
3. Transition is measured ±500mV from steady state voltage with specified loading in Load B.
4. This parameter is sampled and not 100% tested.

●TIMING WAVEFORM OF READ CYCLE NO.1 [1]

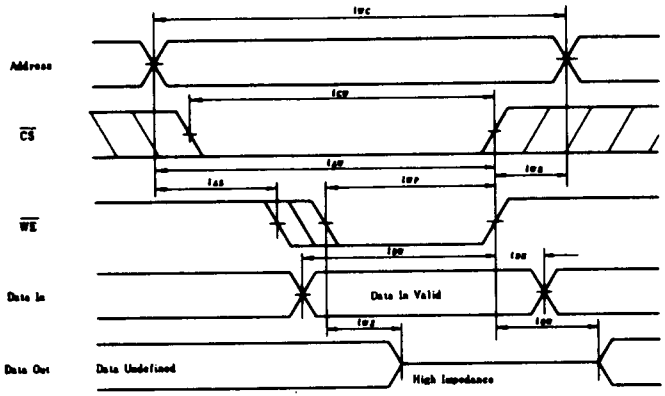


● TIMING WAVEFORM OF READ CYCLE NO. 2 [1), 3)]

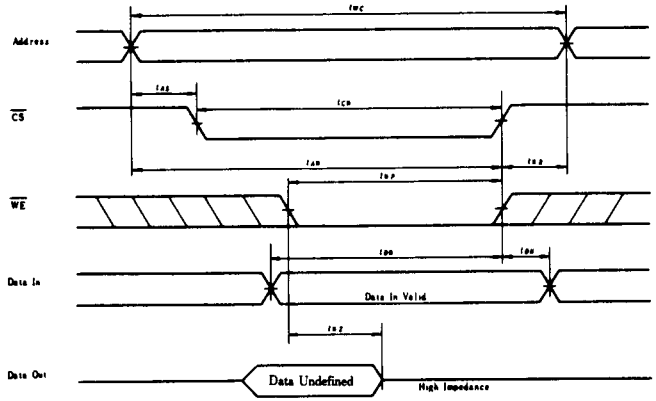


NOTES: 1. $\overline{WE}$ is high and $\overline{CS}$ is low for READ cycle.
2. Addresses valid prior to or coincident with $\overline{CS}$ transition low.
3. Transition is measured ±500 mV from steady state voltage with specified loading in Load B.

● TIMING WAVEFORM OF WRITE CYCLE NO. 1 ($\overline{WE}$ Controlled)



● TIMING WAVEFORM OF WRITE CYCLE No. 2 ($\overline{CS}$ Controlled)



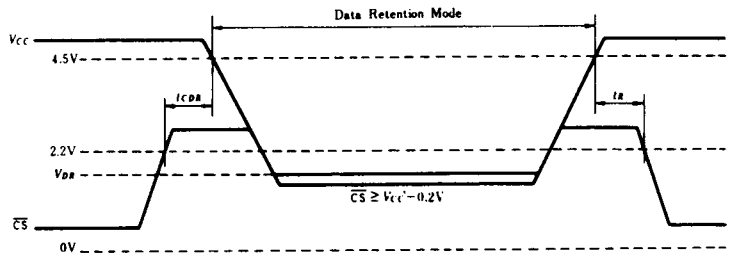
■LOW V_{CC} DATA RETENTION CHARACTERISTICS (Ta=0°C to +70°C)

This characteristics is guaranteed only for L-version.

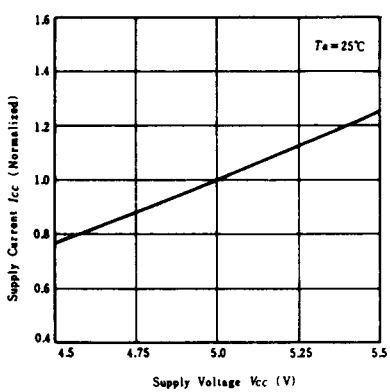
Parameter	Symbol	Test Condition	min	typ	max	Unit
V_{CC} for Data Retention	V_{DR}		2.0	—	—	V
Data Retention Current	I_{CCDR}	$\overline{CS} \geq V_{CC}-0.2V$	—	—	20*2	μA
		$V_{in} \geq V_{CC}-0.2V$ or	—	—	30*3	
Chip Deselect to Data Retention Time	t_{CDR}	$0V \leq V_{in} \leq 0.2V$	0	—	—	ns
Operation Recovery Time	t_R		t_{RC}*1	—	—	ns

Notes) *1. t_{RC}=Read Cycle Time *2. V_{CC}=2.0V
*3. V_{CC}=3.0V

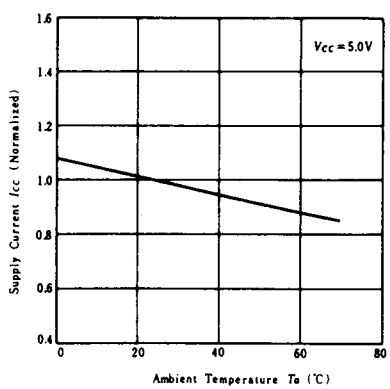
● LOW V_{CC} DATA RETENTION WAVEFORM



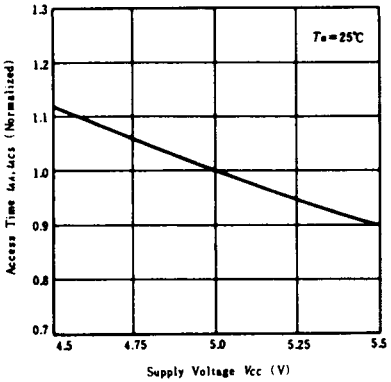
SUPPLY CURRENT vs. SUPPLY VOLTAGE



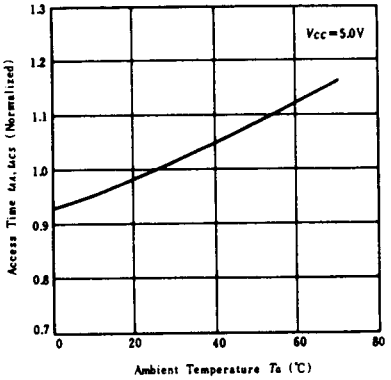
SUPPLY CURRENT vs. AMBIENT TEMPERATURE



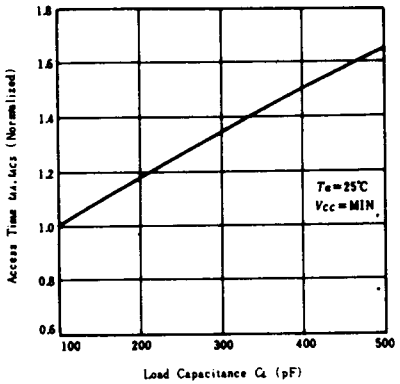
ACCESS TIME vs. SUPPLY VOLTAGE



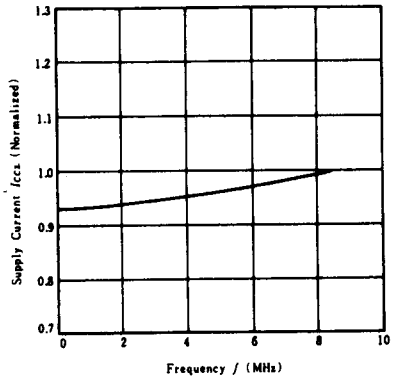
ACCESS TIME vs. AMBIENT TEMPERATURE



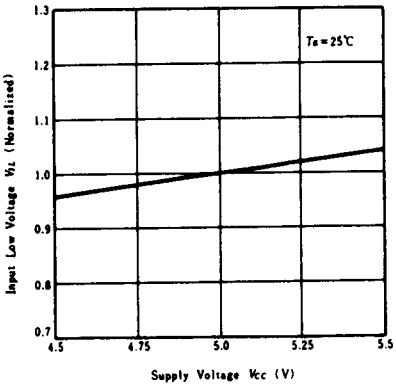
ACCESS TIME vs. LOAD CAPACITANCE



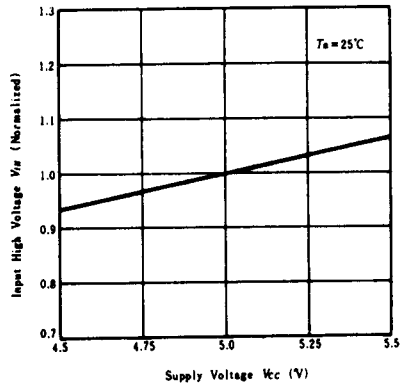
SUPPLY CURRENT vs. FREQUENCY



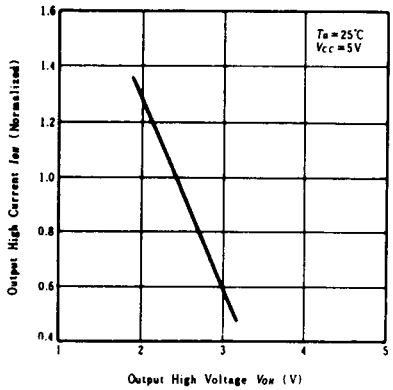
INPUT LOW VOLTAGE vs. SUPPLY VOLTAGE



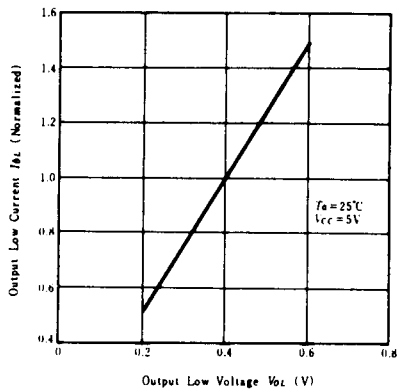
INPUT HIGH VOLTAGE vs. SUPPLY VOLTAGE



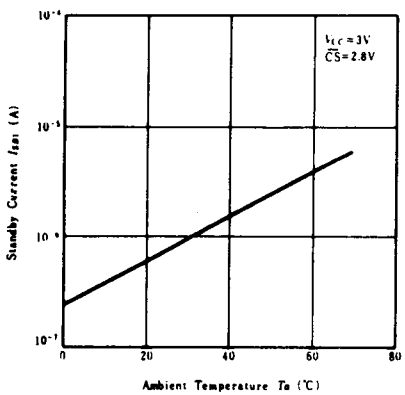
OUTPUT HIGH CURRENT vs. OUTPUT HIGH VOLTAGE



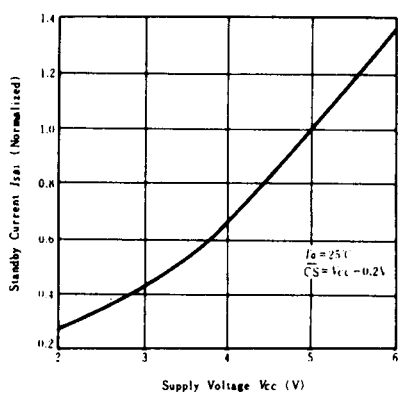
OUTPUT LOW CURRENT vs. OUTPUT LOW VOLTAGE



STANDBY CURRENT vs. AMBIENT TEMPERATURE



STANDBY CURRENT vs. SUPPLY VOLTAGE



STANDBY CURRENT vs. INPUT VOLTAGE